MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPW1R306PL

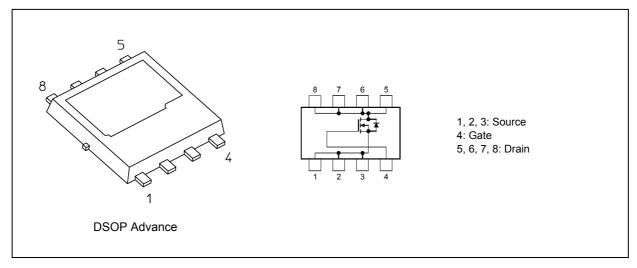
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 22 \text{ nC}$  (typ.)
- (3) Small output charge:  $Q_{oss} = 77.5 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 0.95 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.0 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	60	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(T <sub>c</sub> = 25 °C) (Bottom drain)	(Note 1), (Note 2)	Ι <sub>D</sub>	100	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	260	]
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I <sub>DP</sub>	500	]
Power dissipation	(T <sub>c</sub> = 25 °C) (Bottom drain)		P <sub>D</sub>	170	W
Power dissipation		(Note 3)	P <sub>D</sub>	3.0	]
Power dissipation		(Note 4)	PD	0.96	]
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	552	mJ
Single-pulse avalanche current		(Note 5)	I <sub>AS</sub>	50	A
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristic	Symbol	Max	Unit		
Channel-to-case thermal resistance	Bottom drain (T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	0.88	°C/W
Channel-to-case thermal resistance	Top source (T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	0.93	
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 3)	R <sub>th(ch-a)</sub>	50	]
Channel-to-ambient thermal resistance	(T <sub>a</sub> = 25 °C)	(Note 4)	R <sub>th(ch-a)</sub>	156	

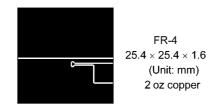
Note 1: Ensure that the channel temperature does not exceed 175 °C.

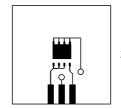
Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

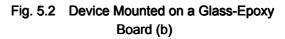
Note 5: V\_DD = 48 V, T\_ch = 25 °C (initial), L = 170  $\mu$ H, I<sub>AS</sub> = 50 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

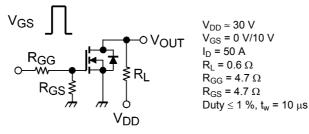
### 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	$V_{DS}$ = 60 V, $V_{GS}$ = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60	_	—	V
Drain-source breakdown voltage (Note 6)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	45		_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	1.5	_	2.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 42 A	_	1.5	2.3	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		0.95	1.29	

Note 6: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	6250	8100	pF
Reverse transfer capacitance	C <sub>rss</sub>		—	80	—	
Output capacitance	C <sub>oss</sub>		_	1160	—	
Gate resistance	r <sub>g</sub>	—	_	0.5	1.0	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	8.3	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	20	—	
Switching time (fall time)	t <sub>f</sub>	]	_	14.7	_	
Switching time (turn-off time)	t <sub>off</sub>		_	70	_	



#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

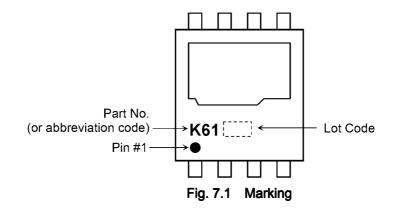
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 30$ V, $V_{GS}$ = 10 V, $I_D$ = 50 A	_	91	_	nC
gate-drain)		$V_{DD} \approx 30$ V, $V_{GS}$ = 4.5 V, $I_D$ = 42 A	_	44	_	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 30$ V, $V_{GS}$ = 10 V, $I_D$ = 50 A	_	17.3	—	
Gate-drain charge	Q <sub>gd</sub>		_	14.4	—	
Gate switch charge	Q <sub>SW</sub>		_	22	_	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	77.5	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

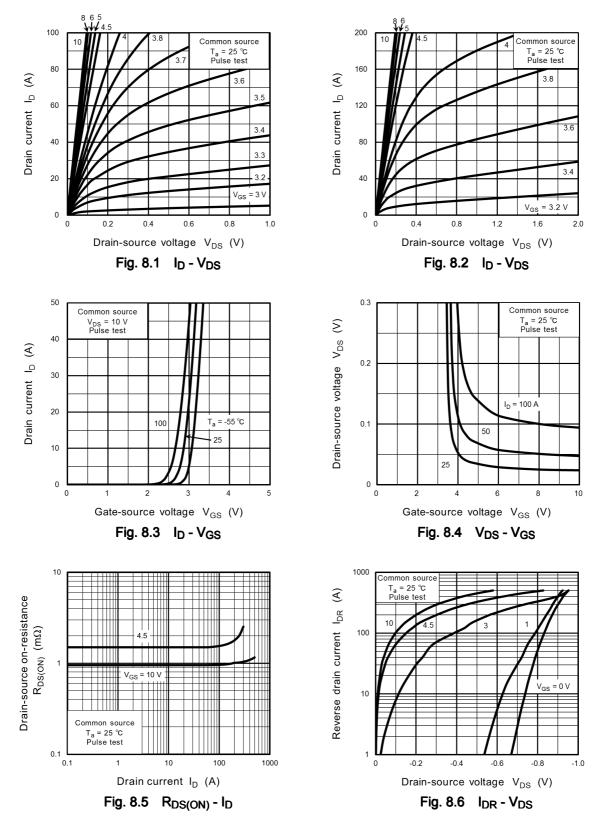
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7	) I <sub>DRP</sub> (t = 100 μs)	—	—	—	500	A
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 100 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V
Reverse recovery time	t <sub>rr</sub>	V <sub>R</sub> = 30 V, I <sub>DR</sub> = 25 A,	_	47	_	ns
Reverse recovery charge	Q <sub>rr</sub>	V <sub>GS</sub> = 0 V, -dI <sub>DR</sub> /dt = 100 A/μs		48	_	nC

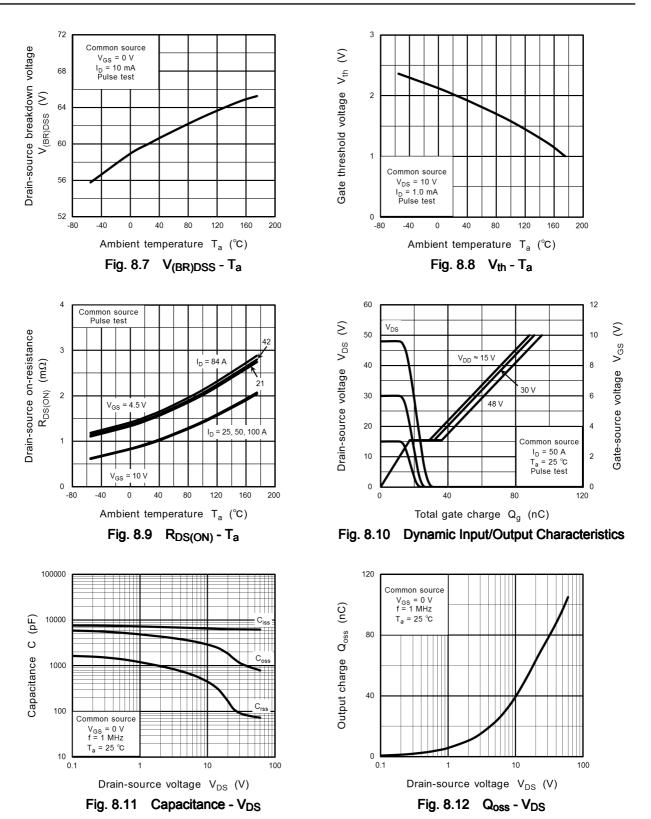
Note 7: Ensure that the channel temperature does not exceed 175 °C.

### 7. Marking

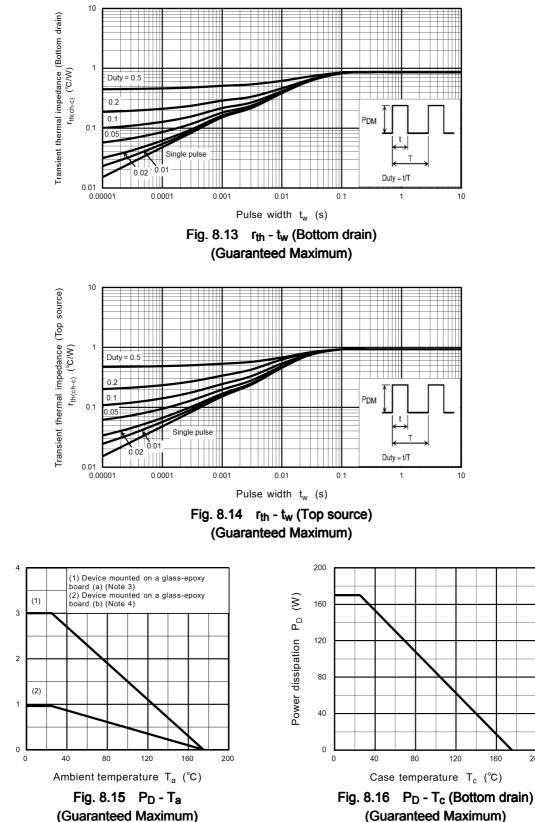


### 8. Characteristics Curves (Note)





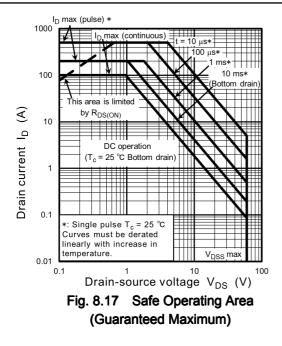




Power dissipation PD (W)

200



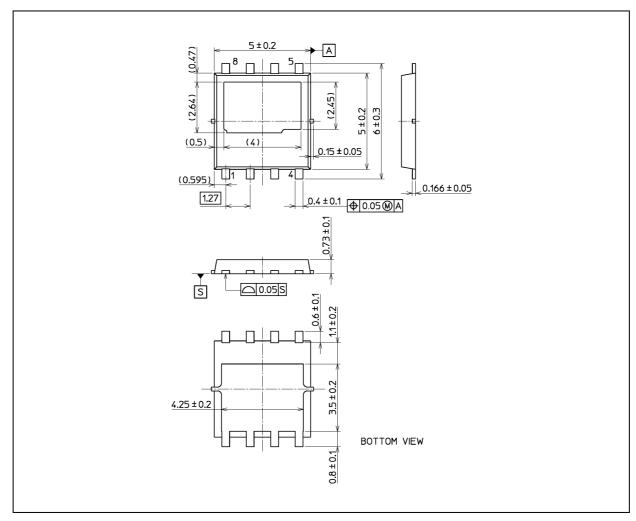


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPW1R306PL

#### **Package Dimensions**

Unit: mm



Weight: 0.104 g (typ.)

Package Name(s)

TOSHIBA: 2-5S1A

Nickname: DSOP Advance

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